

**DL-3038-011**

Index Guided AlGaInP Laser Diode

Overview

DL-3038-011 is index guided 635 nm (Typ.) AlGaInP laser diode.

The low threshold current and short wavelength are achieved by a strained multiple quantum well active layer.

The lasing wavelength is the same as He-Ne gas lasers. DL-3038-011 is suitable for laser pointers.

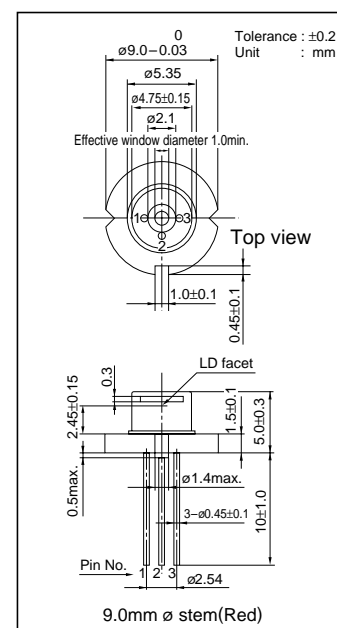
Features

- Short wavelength : 635 nm (Typ.)
- High output power : 5 mW CW
- Low threshold current : $I_{th} = 40$ mA (Typ.)
- Low operating voltage : $V_{op} = 2.2$ V (Typ.)

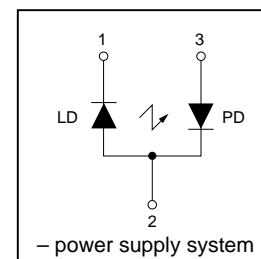
Absolute Maximum Ratings at $T_c=25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Light Output	P_o	5	mW
Reverse Voltage	Laser PIN V_R	2	V
		30	
Operating Temperature	T_{opr}	-10 to +40	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +85	$^\circ\text{C}$

Package Dimensions



Electrical Connection



Electrical and Optical Characteristics at $T_c=25^\circ\text{C}$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold Current	I_{th}	CW	-	40	70	mA
Operating Current	I_{op}	$P_o=5\text{mW}$	-	55	85	mA
Operating Voltage	V_{op}	$P_o=5\text{mW}$	-	2.2	2.4	V
Lasing Wavelength	λ_p	$P_o=5\text{mW}$	-	635	640	nm
Beam \ast) Divergence	Perpendicular	θ_\perp	$P_o=5\text{mW}$	25	35	deg.
	Parallel	θ_\parallel	$P_o=5\text{mW}$	6	8	deg.
Off Axis Angle	Perpendicular	$\Delta\theta_\perp$	-	-	± 3	deg.
	Parallel	$\Delta\theta_\parallel$	-	-	± 3	deg.
Differential Efficiency	dP_o/dI_{op}	-	0.1	0.3	-	mW/mA
Monitoring Output Current	I_m	$P_o=5\text{mW}$	0.05	0.2	-	mA
Astigmatism	A_s	$P_o=5\text{mW}$	-	8	-	μm

\ast) Full angle at half maximum note : The above product specifications are subject to change without notice.

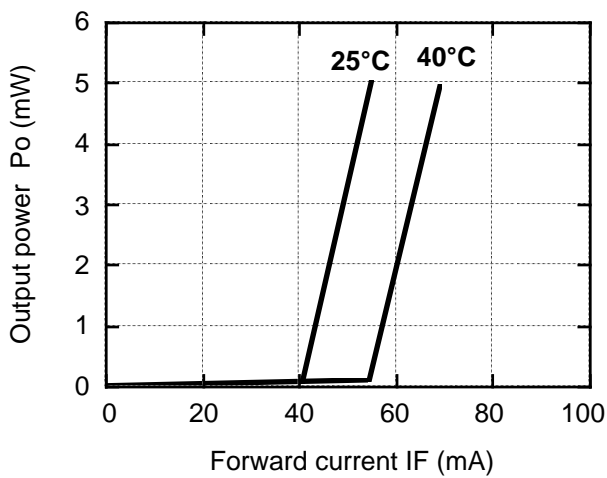
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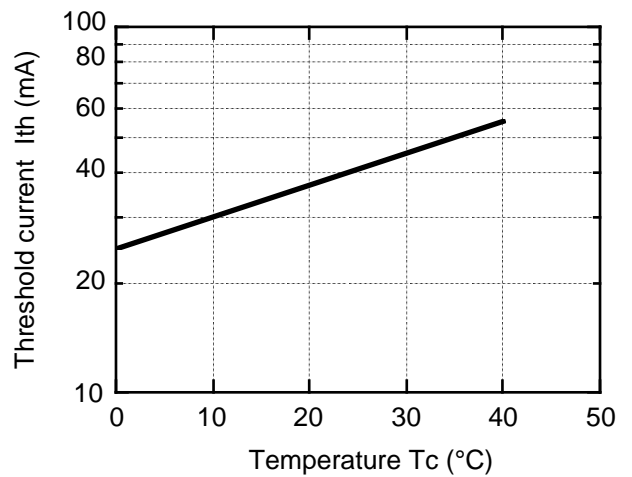
N2798 GI / N2897 GI, (IM) No.5853 1/3

Characteristics

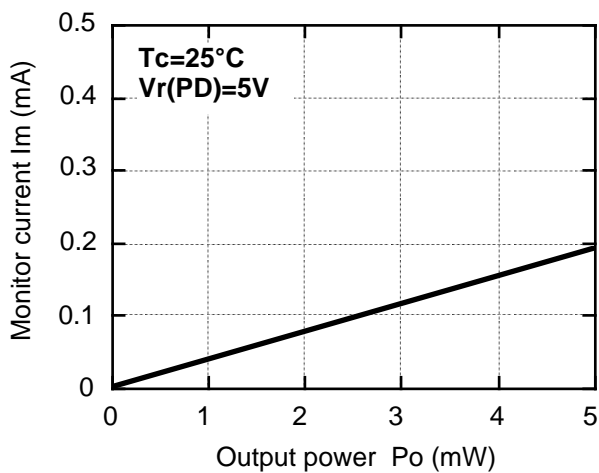
Output power vs. Forward current



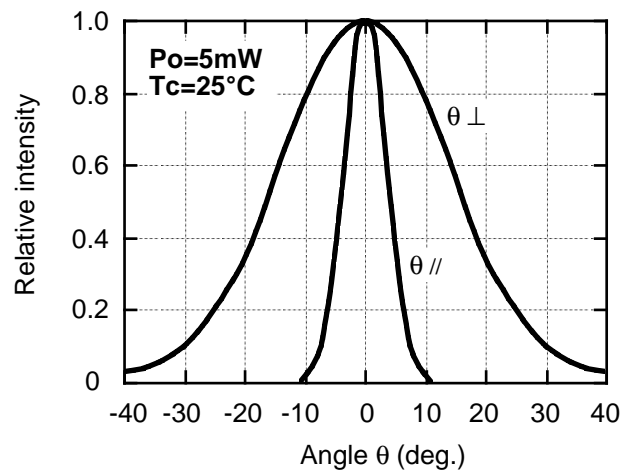
Threshold current vs. Temperature



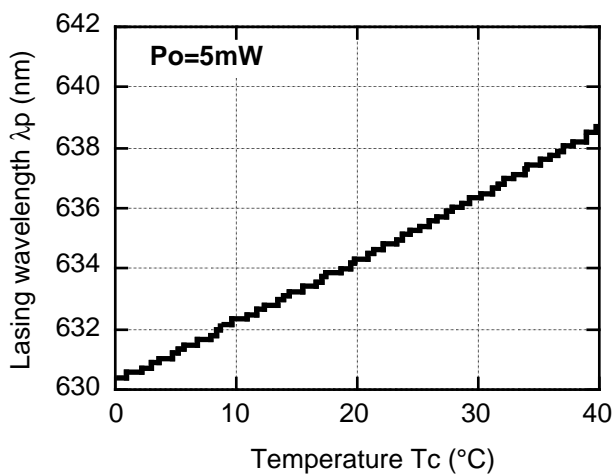
Monitor current vs. Output power



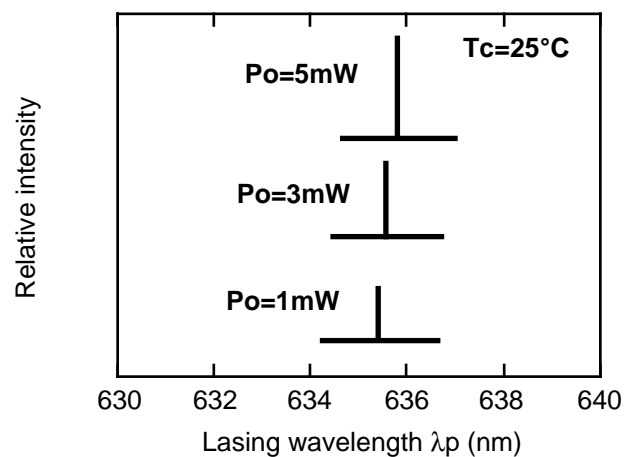
Beam divergence



Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength





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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

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